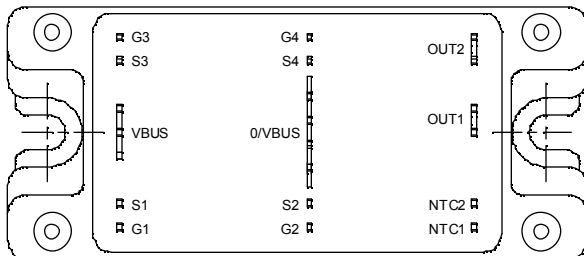
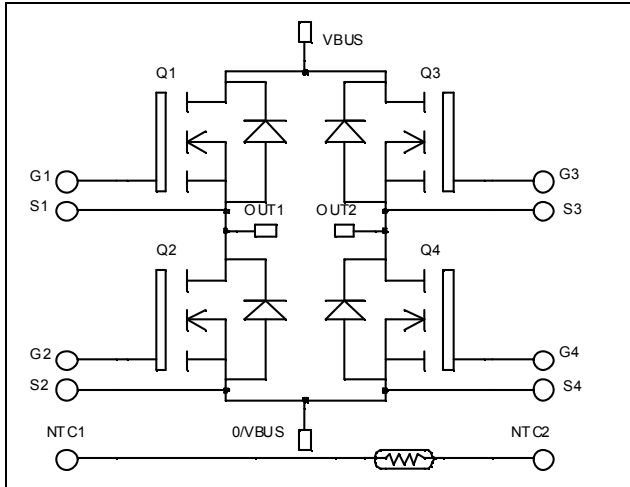


Full - Bridge MOSFET Power Module

$V_{DSS} = 1200V$
 $R_{DSon} = 570m\Omega$ typ @ $T_j = 25^\circ C$
 $I_D = 17A$ @ $T_c = 25^\circ C$



Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features


- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1200	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	17
		$T_c = 80^\circ C$	13
I_{DM}	Pulsed Drain current	68	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	684	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	390
I_{AR}	Avalanche current (repetitive and non repetitive)	22	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	


CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 1200\text{V}$			250	μA
		$V_{GS} = 0\text{V}, V_{DS} = 1000\text{V}$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 8.5\text{A}$		570	684	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			± 100	nA

Dynamic Characteristics

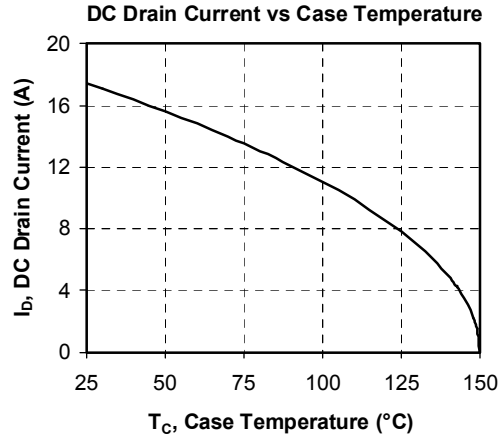
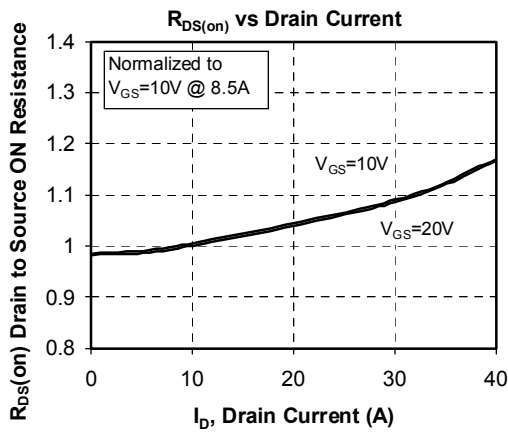
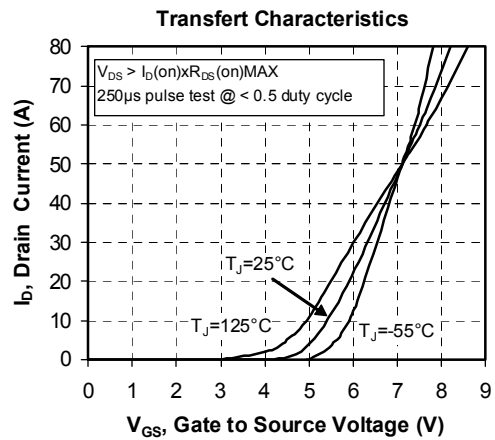
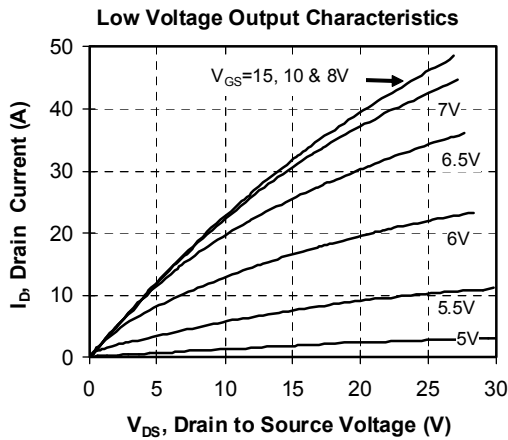
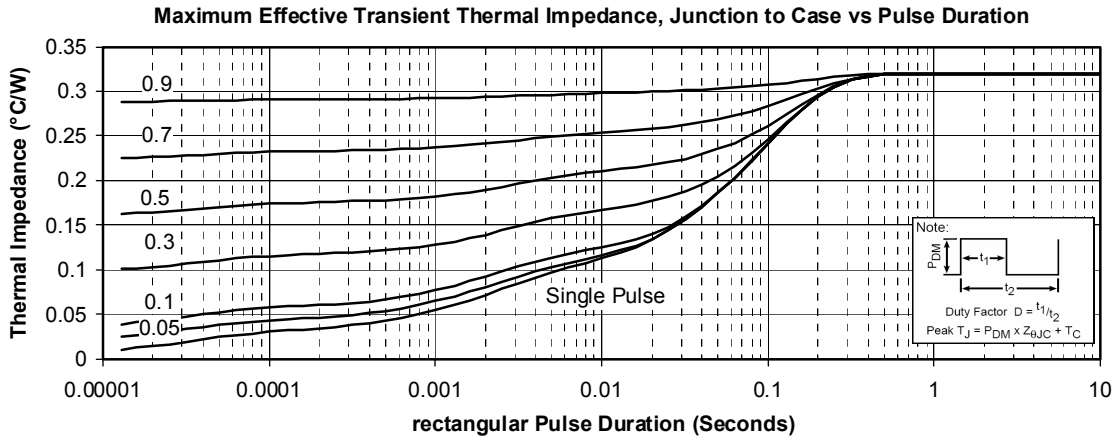
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		5155		pF
C_{oss}	Output Capacitance			770		
C_{rss}	Reverse Transfer Capacitance			130		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 600\text{V}$ $I_D = 17\text{A}$		187		nC
Q_{gs}	Gate – Source Charge			24		
Q_{gd}	Gate – Drain Charge			120		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15\text{V}$ $V_{Bus} = 800\text{V}$ $I_D = 17\text{A}$ $R_G = 5\Omega$		20		ns
T_r	Rise Time			15		
$T_{d(off)}$	Turn-off Delay Time			160		
T_f	Fall Time			45		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15\text{V}, V_{Bus} = 800\text{V}$ $I_D = 17\text{A}, R_G = 5\Omega$		990		μJ
E_{off}	Turn-off Switching Energy			685		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15\text{V}, V_{Bus} = 800\text{V}$ $I_D = 17\text{A}, R_G = 5\Omega$		1565		μJ
E_{off}	Turn-off Switching Energy			857		

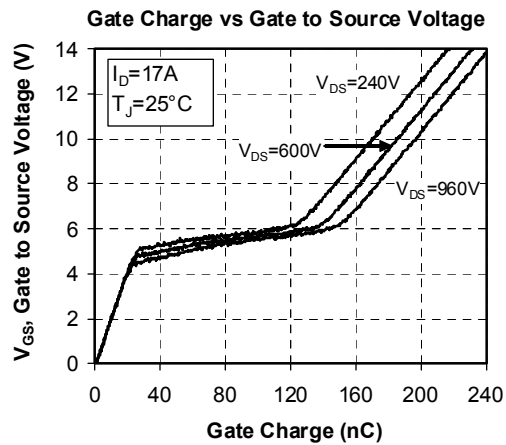
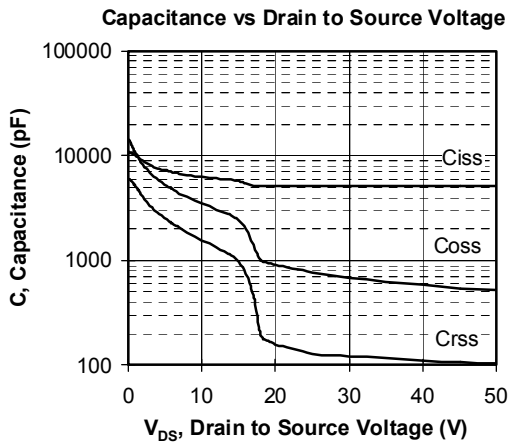
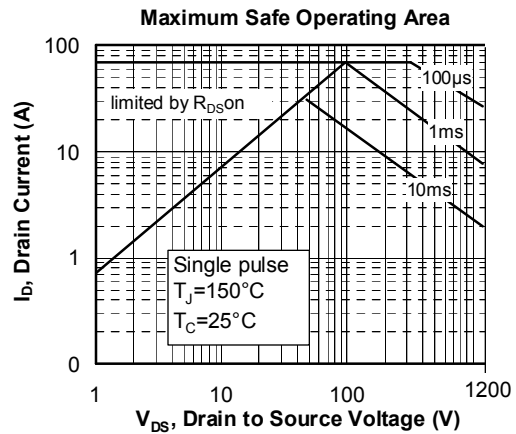
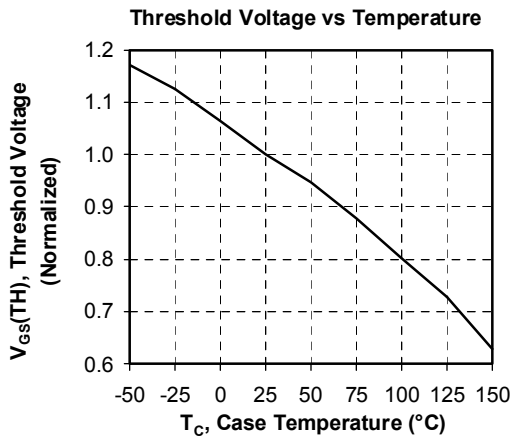
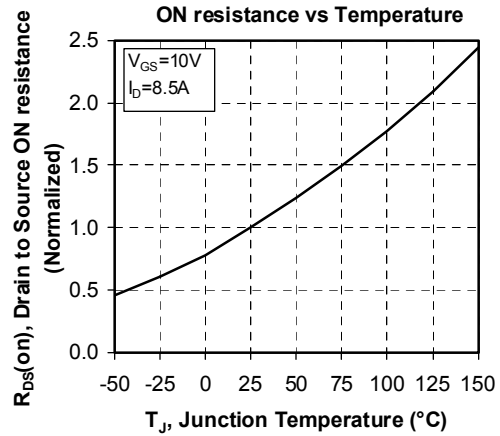
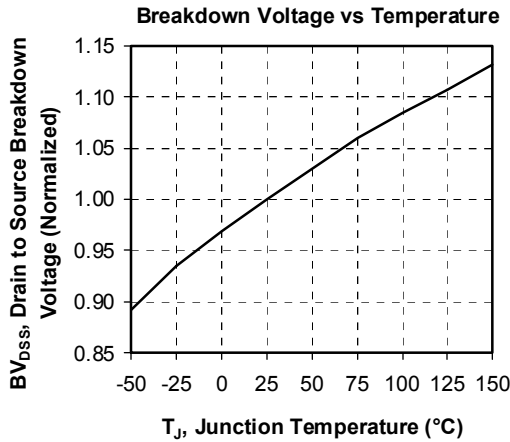
Source - Drain diode ratings and characteristics

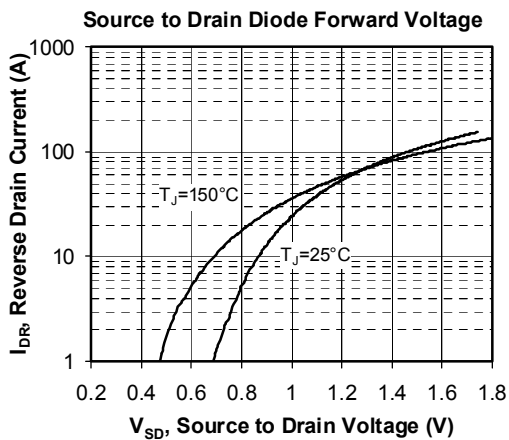
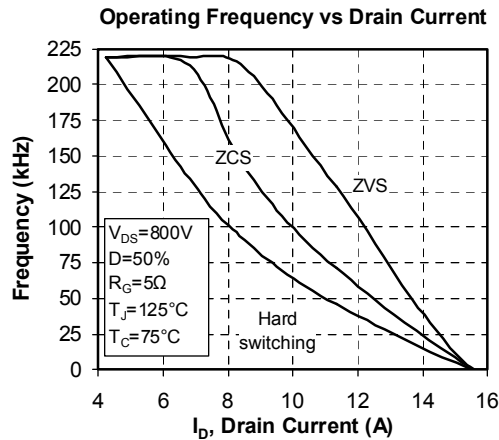
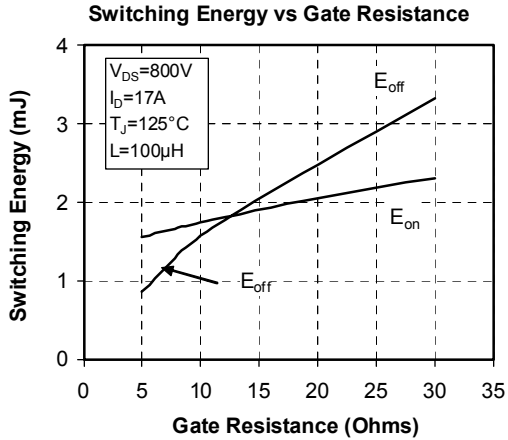
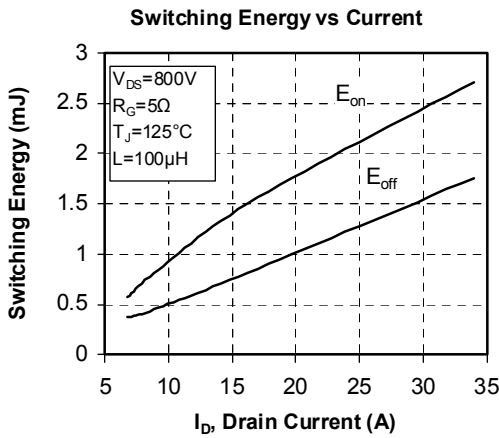
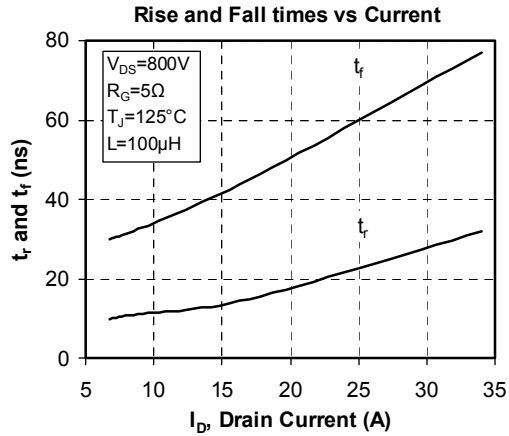
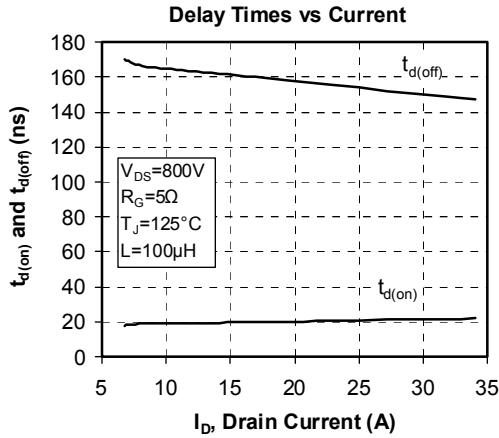
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)		$T_c = 25^\circ\text{C}$		17	A
			$T_c = 80^\circ\text{C}$		13	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -17\text{A}$			1.3	V
dv/dt	Peak Diode Recovery ①				18	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -17\text{A}$ $V_R = 600\text{V}$ $di_S/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		320	ns
			$T_j = 125^\circ\text{C}$		650	
Q_{rr}	Reverse Recovery Charge	$I_S = -17\text{A}$ $V_R = 600\text{V}$ $di_S/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	2		μC
			$T_j = 125^\circ\text{C}$	7		

 ① dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -17\text{A} \quad di/dt \leq 700\text{A}/\mu\text{s} \quad V_R \leq V_{DSS} \quad T_j \leq 150^\circ\text{C}$$

Typical Performance Curve






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